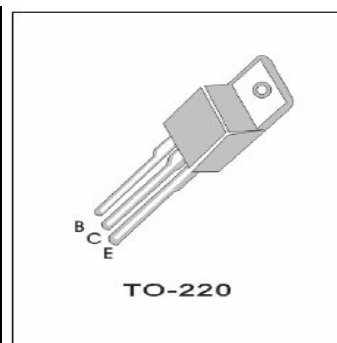


**EB SERIES TRANSISTORS****E3150**● **FEATURES:** ①HIGH VOLTAGE CAPABILITY ②HIGH SPEED SWITCHING ③WIDE SOA● **APPLICATION:** ①FLUORESCENT LAMP ②ELECTRONIC BALLAST● **Absolute Maximum Ratings (Tc=25℃)**

TO-220 NPN

PARAMETER	SYMBOL	VALUE	UNIT
Collector–Base Voltage	V _{CB0}	700	V
Collector–Emitter Voltage	V _{CEO}	600	V
Emitter –Base Voltage	V _{EBO}	9	V
Collector Current	I _C	1.5	A
Junction Temperature	T _j	150	℃
Storage Temperature	T _{stg}	-65-150	℃

● **Electronic Characteristics (Tc=25℃)**

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector–Base Cutoff Current	I _{CBO}	V _{CB} =700v		100	μA
Collector–Emitter Cutoff Current	I _{CEO}	V _{CE} =600v		250	μA
Collector–Emitter Voltage	V _{CEO}	I _C =10mA I _B =0	600		V
Emitter –Base Voltage	V _{EBO}	I _E =1mA I _C =0	9		V
Collector–Emitter Saturation Voltage	V _{cesat}	I _C =1A I _B =0.25A		1.0	V
Base–Emitter Saturation Voltage	V _{besat}	I _C =0.5A I _B =0.1A		1.2	V
DC Current Gain	HFE	V _{CE} =5v I _C =1mA	7		
		V _{CE} =5v I _C =0.2A	10	40	
		V _{CE} =5v I _C =1.0A	5		

● **CLASSIFICATION OF HFE**

HFE	15-20	20-25	25-30	30-35
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EB SERIES TRANSISTORS

E3150

TO-220 MECHANICAL DATA

SYMBOL	Min	Nom	Max	SYMBOL	Min	Nom	Max
A	3.5	4.5	5.0	L	12.5	13.5	14.5
B	1.25	1.35	1.5	L1	2.5	3.37	4.5
B1	0.75	0.85	0.955	D1	5.9	6.5	7.1
b	0.6			ϕb			1.2
c	0.35	0.43	0.55	Q	1.5	2.5	3.5
D	14.0	15.5	16.5	Q1	2.0	2.6	3.5
E	9.0	10.0	11.0	Z	3.0	3.8	4.5
e		2.54					

